

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
40V	1.2mΩ@10V	235A
	1.6mΩ@4.5V	



合肥矽普半导体

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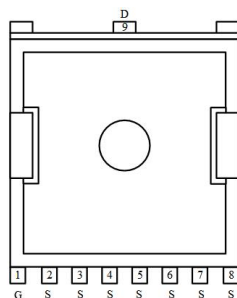
Feature

- Fast Switching
- Low Gate Charge and Rdson
- Advanced Split Gate Trench Technology
- 100% Single Pulse avalanche energy Test

Applications

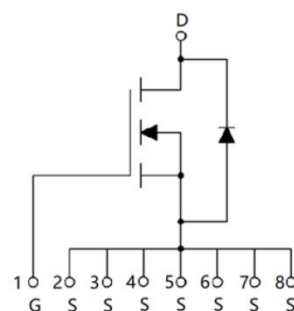
- PWM Application
- Hard switched and high frequency circuits
- Power Management

Package

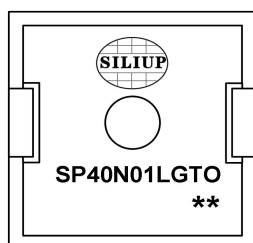


TOLL

Circuit diagram



Marking



SP40N01LGTO :Device Code
** :Week Code

Order Information

Device	Package	Unit/Tape
SP40N01LGTO	TOLL	2000

Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current (Tc=25°C)	I_D	235	A
Continuous Drain Current (Tc=100°C)	I_D	150	A
Pulsed Drain Current	I_{DM}	940	A
Single Pulse Avalanche Energy ¹	E_{AS}	900	mJ
Power Dissipation (Tc=25°C)	P_D	116	W
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	1.08	°C/W
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C

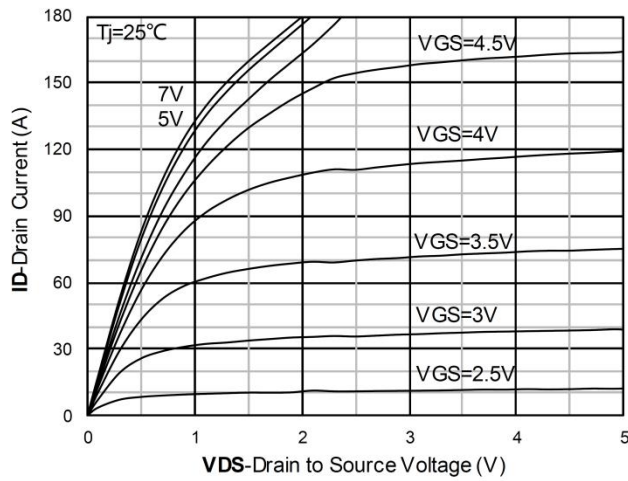
Electrical characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V , ID=250uA	40	45	-	V
Drain-Source Leakage Current	IDSS	VDS=32V , VGS=0V , TJ=25℃	-	-	1	uA
Gate-Source Leakage Current	IGSS	VGS=±20V , VDS=0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	VGS=VDS , ID =250uA	1	1.7	2.5	V
Static Drain-Source On-Resistance	RDS(ON)	VGS=10V , ID=20A	-	1.2	1.5	mΩ
		VGS=4.5V , ID=20A	-	1.6	2.1	
Dynamic characteristics						
Input Capacitance	Ciss	VDS=20V , VGS=0V , f=1MHz	-	5025	-	pF
Output Capacitance	Coss		-	1683	-	
Reverse Transfer Capacitance	Crss		-	63	-	
Total Gate Charge	Qg	VDS=20V , VGS=10V , ID=85A	-	78	-	nC
Gate-Source Charge	Qgs		-	27	-	
Gate-Drain Charge	Qgd		-	16	-	
Switching Characteristics						
Turn-On Delay Time	Td(on)	VDD=20V , VGS=10V , RG=1.6Ω, ID=85A	-	12.3	-	nS
Rise Time	Tr		-	8	-	
Turn-Off Delay Time	Td(off)		-	47.5	-	
Fall Time	Tf		-	8.8	-	
Diode Characteristics						
Diode Forward Voltage	VSD	VGS=0V , IS=1A , TJ=25℃	-	-	1.2	V
Maximum Body-Diode Continuous Current	IS		-	-	235	A
Reverse Recovery Time	Trr	IS=50A , di/dt=100A/us , TJ=25℃	-	64	-	nS
Reverse Recovery Charge	Qrr		-	86.8	-	nC

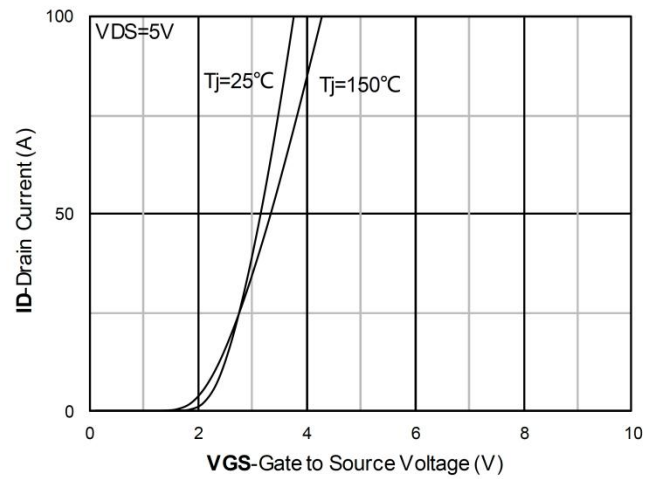
Note :

1. The test condition is $V_{DD}=20V, V_{GS}=10V, L=0.5mH, R_G=25\Omega$

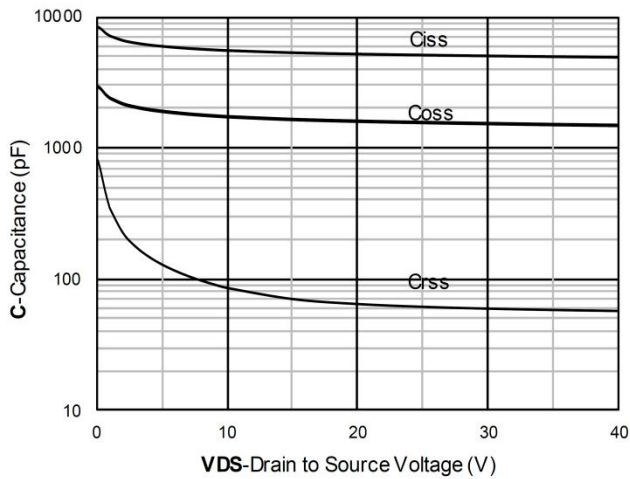
Typical Characteristics



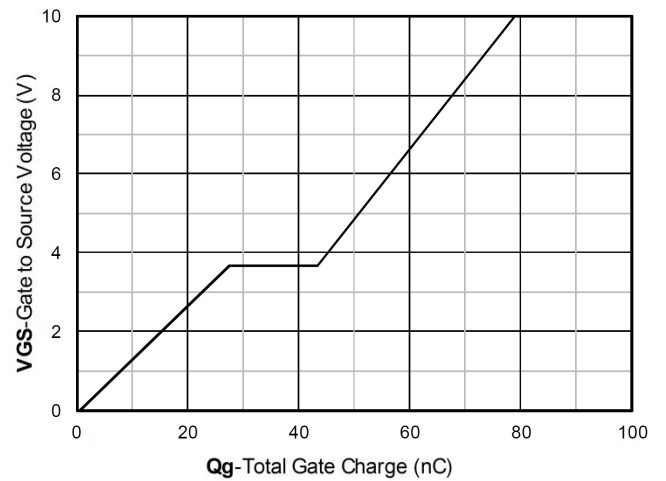
Output Characteristics



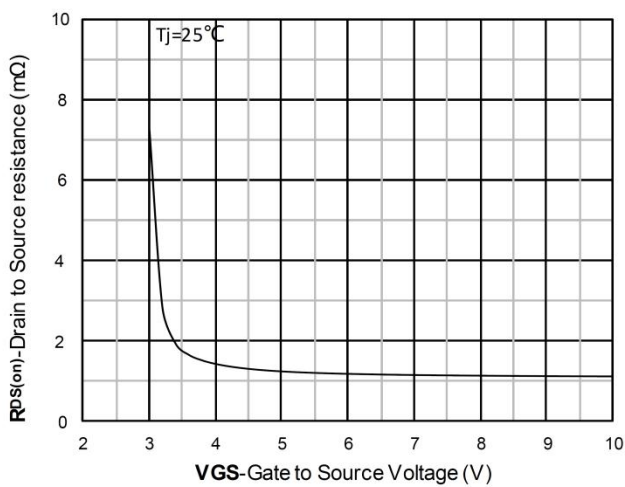
Transfer Characteristics



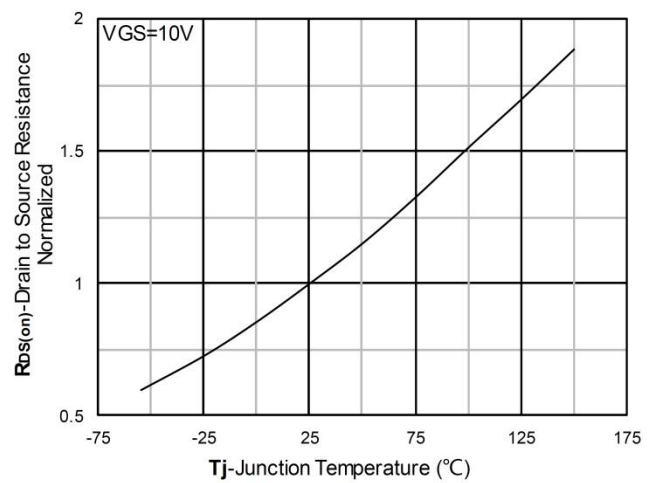
Capacitance Characteristics



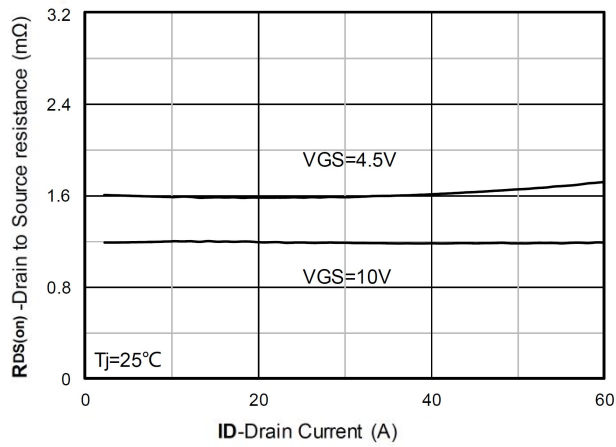
Gate Charge



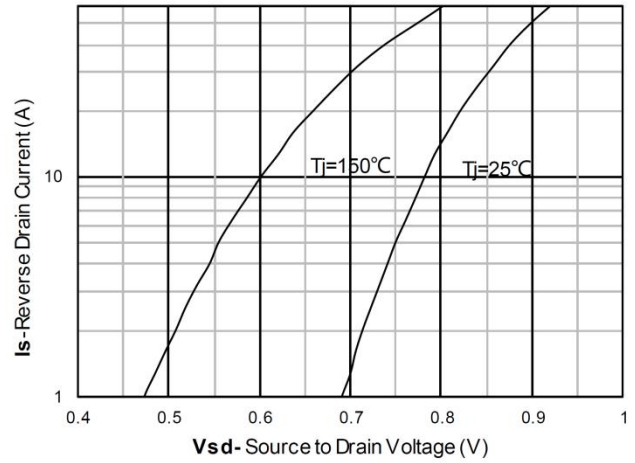
On-Resistance vs Gate to Source Voltage



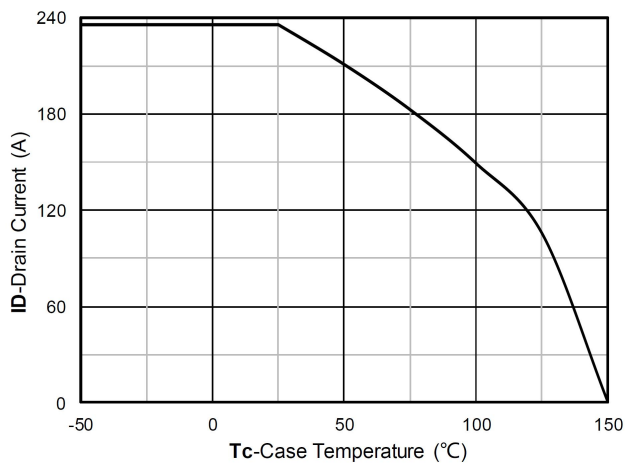
Normalized On-Resistance



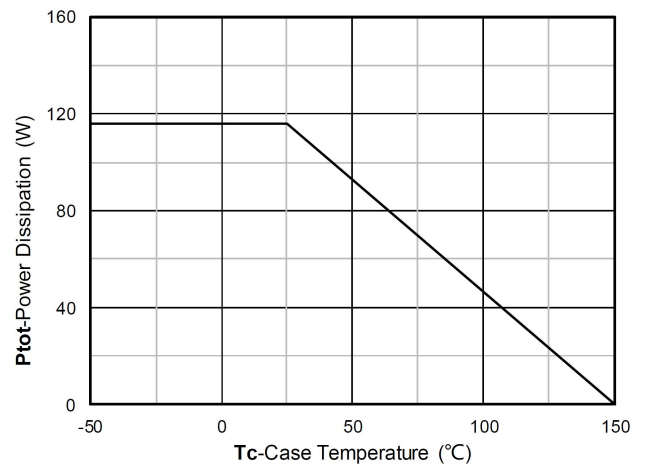
RDS(on) VS Drain Current



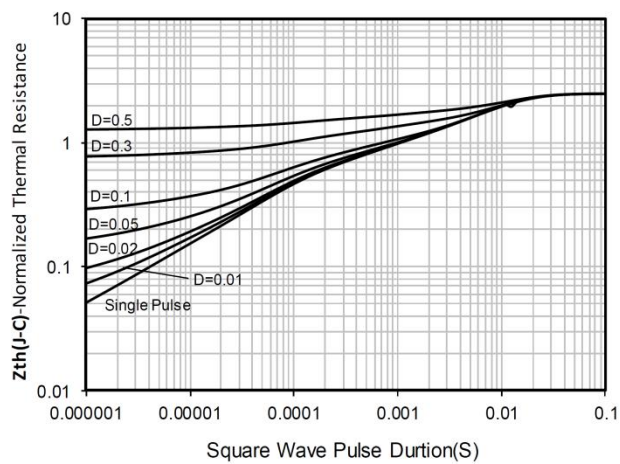
Forward characteristics of reverse diode



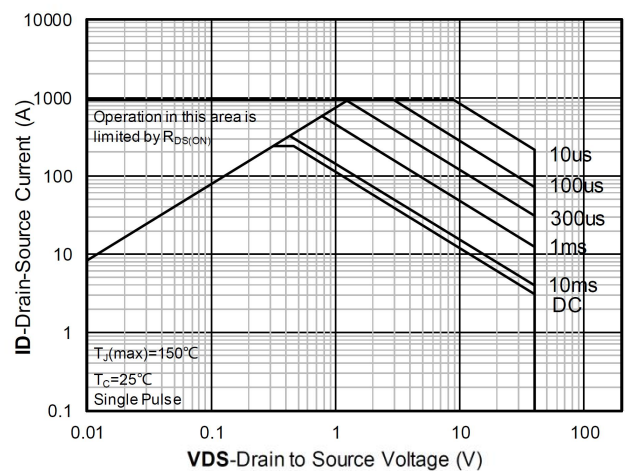
Current dissipation



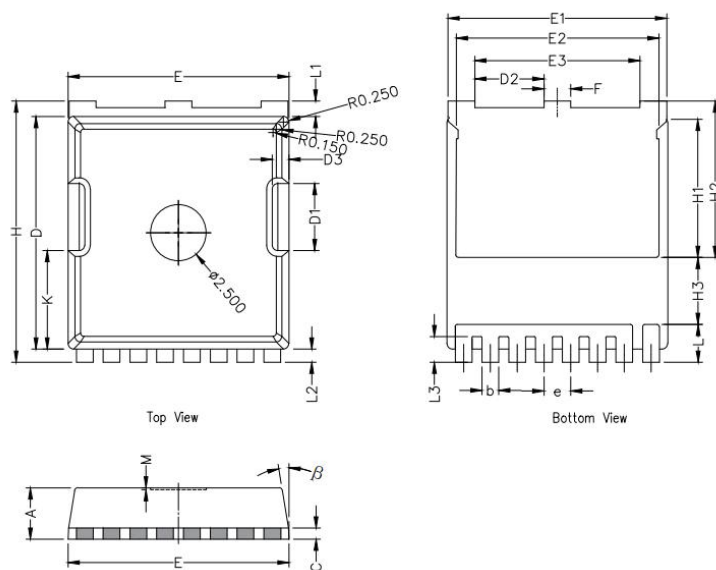
Power dissipation



Maximum Transient Thermal Impedance



Safe Operation Area

TOLL Package Information


Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	2.20	2.30	2.40
b	0.65	0.75	0.85
C	0.508 REF		
D	10.25	10.40	10.55
D1	2.85	3.00	3.15
E	9.75	9.90	10.05
E1	9.65	9.80	9.95
E2	8.95	9.10	9.25
E3	7.25	7.40	7.55
e	1.20 BSC		
F	1.05	1.20	1.35
H	11.55	11.70	11.85
H1	6.03	6.18	6.33
H2	6.85	7.00	7.15
H3	3.00 BSC		
L	1.55	1.70	1.85
L1	0.55	0.7	0.85
L2	0.45	0.6	0.75
M	0.08 REF.		
β	8°	10°	12°
K	4.25	4.40	4.55